

# DATA SHEET

## **BU506; BU506D** Silicon diffused power transistors

Product specification  
Supersedes data of December 1991  
File under Discrete Semiconductors, SC06

1997 Aug 13

# Silicon diffused power transistors

# BU506; BU506D

## DESCRIPTION

High-voltage, high-speed, switching NPN power transistor in a TO-220AB package. The BU506D has an integrated efficiency diode.

## APPLICATIONS

- Horizontal deflection circuits of colour television receivers
- Line-operated switch-mode applications.

## PINNING

| PIN | DESCRIPTION                           |
|-----|---------------------------------------|
| 1   | base                                  |
| 2   | collector; connected to mounting base |
| 3   | emitter                               |

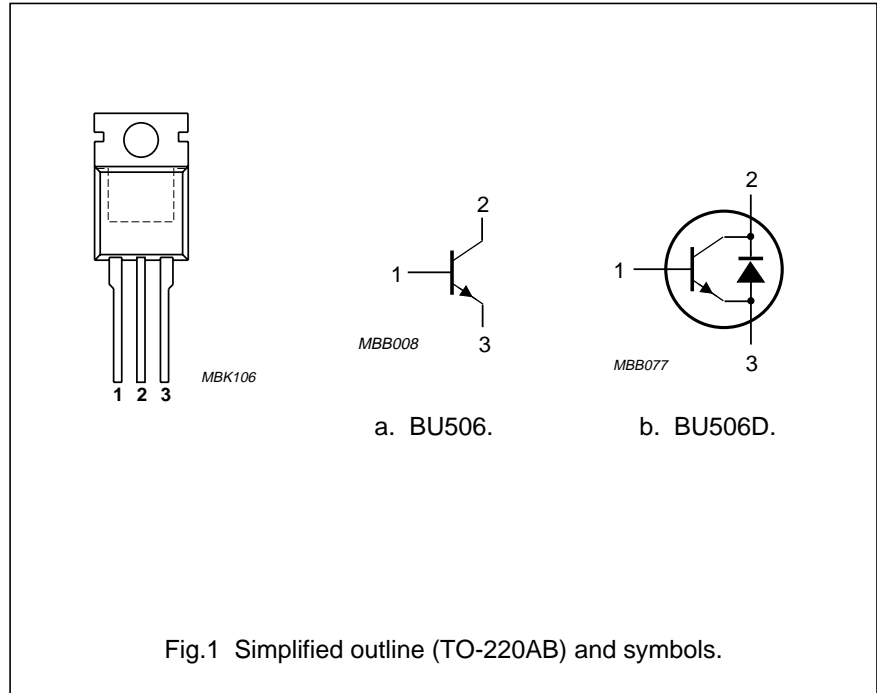


Fig.1 Simplified outline (TO-220AB) and symbols.

## QUICK REFERENCE DATA

| SYMBOL      | PARAMETER                            | CONDITIONS                                             | TYP. | MAX. | UNIT          |
|-------------|--------------------------------------|--------------------------------------------------------|------|------|---------------|
| $V_{CESM}$  | collector-emitter peak voltage       | $V_{BE} = 0$                                           | –    | 1500 | V             |
| $V_{CEO}$   | collector-emitter voltage            | open base                                              | –    | 700  | V             |
| $V_{CESat}$ | collector-emitter saturation voltage | $I_C = 3\text{ A}$ ; $I_B = 1.33\text{ A}$ ; see Fig.6 | –    | 1    | V             |
| $V_F$       | diode forward voltage (BU506D)       | $I_F = 3\text{ A}$ ; see Fig.10                        | 1.5  | –    | V             |
| $I_{Csat}$  | collector saturation current         |                                                        | –    | 3    | A             |
| $I_C$       | collector current (DC)               | see Fig.2                                              | –    | 5    | A             |
| $I_{CM}$    | collector current (peak value)       | see Fig.2                                              | –    | 8    | A             |
| $P_{tot}$   | total power dissipation              | $T_{mb} \leq 25\text{ }^\circ\text{C}$ ; see Fig.3     | –    | 100  | W             |
| $t_f$       | fall time                            | inductive load; see Fig.9                              | 0.7  | –    | $\mu\text{s}$ |

## THERMAL CHARACTERISTICS

| SYMBOL         | PARAMETER                                         | VALUE | UNIT |
|----------------|---------------------------------------------------|-------|------|
| $R_{th\ j-mb}$ | thermal resistance from junction to mounting base | 1.25  | K/W  |

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL     | PARAMETER                      | CONDITIONS                             | MIN. | MAX. | UNIT |
|------------|--------------------------------|----------------------------------------|------|------|------|
| $V_{CESM}$ | collector-emitter peak voltage | $V_{BE} = 0$                           | –    | 1500 | V    |
| $V_{CEO}$  | collector-emitter voltage      | open base                              | –    | 700  | V    |
| $I_{CSat}$ | collector saturation current   |                                        | –    | 3    | A    |
| $I_C$      | collector current (DC)         | see Fig.2                              | –    | 5    | A    |
| $I_{CM}$   | collector current (peak value) | see Fig.2                              | –    | 8    | A    |
| $I_B$      | base current (DC)              |                                        | –    | 3    | A    |
| $I_{BM}$   | base current (peak value)      |                                        | –    | 5    | A    |
| $P_{tot}$  | total power dissipation        | $T_{mb} \leq 25\text{ °C}$ ; see Fig.3 | –    | 100  | W    |
| $T_{stg}$  | storage temperature            |                                        | –65  | +150 | °C   |
| $T_j$      | junction temperature           |                                        | –    | 150  | °C   |

**CHARACTERISTICS**

$T_j = 25\text{ °C}$  unless otherwise specified.

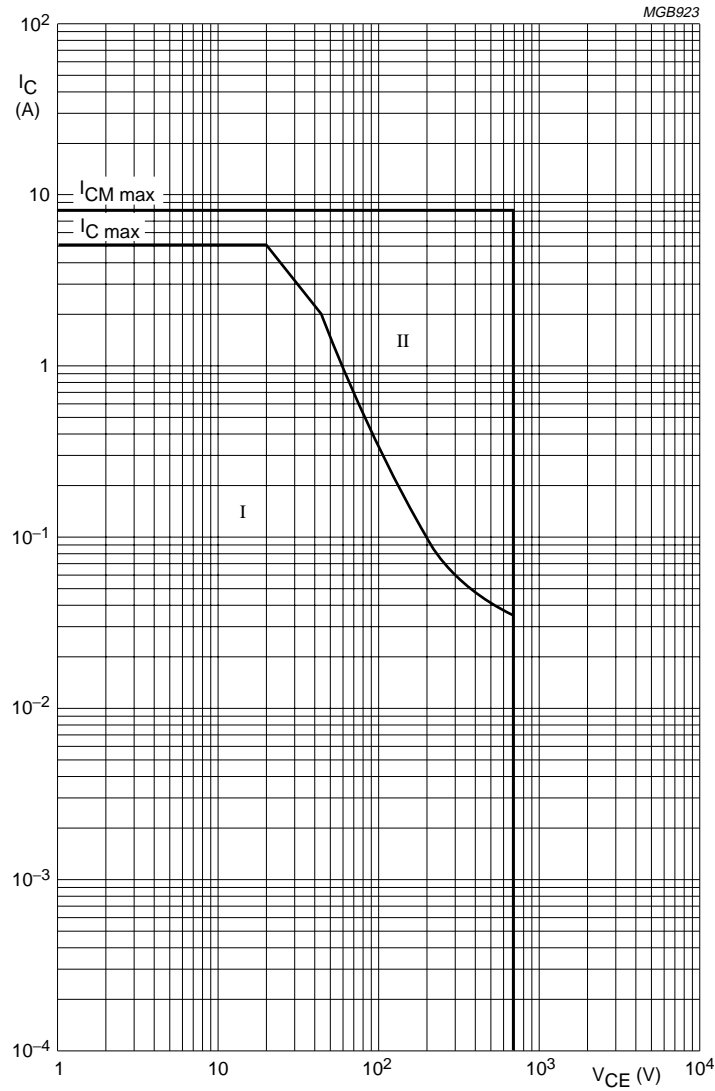
| SYMBOL                                                              | PARAMETER                            | CONDITIONS                                                                           | MIN. | TYP. | MAX. | UNIT          |
|---------------------------------------------------------------------|--------------------------------------|--------------------------------------------------------------------------------------|------|------|------|---------------|
| $V_{CEOsust}$                                                       | collector-emitter sustaining voltage | see Figs 4 and 5                                                                     | 700  | –    | –    | V             |
| $V_{CESat}$                                                         | collector-emitter saturation voltage | $I_C = 3\text{ A}$ ; $I_B = 1.33\text{ A}$ ; see Fig.6                               | –    | –    | 1    | V             |
| $V_{BEsat}$                                                         | base-emitter saturation voltage      | $I_C = 3\text{ A}$ ; $I_B = 1.33\text{ A}$ ; see Fig.7                               | –    | –    | 1.3  | V             |
| $V_F$                                                               | diode forward voltage (BU506D)       | $I_F = 3\text{ A}$ ; see Fig.10                                                      | –    | 1.5  | 2.2  | V             |
| $I_{CES}$                                                           | collector-emitter cut-off current    | $V_{CE} = V_{CESmax}$ ; $V_{BE} = 0$ ; note 1                                        | –    | –    | 0.5  | mA            |
|                                                                     |                                      | $V_{CE} = V_{CESmax}$ ; $V_{BE} = 0$ ;<br>$T_j = 125\text{ °C}$ ; note 1             | –    | –    | 1    | mA            |
| $I_{EBO}$                                                           | emitter-base cut-off current         | $V_{EB} = 6\text{ V}$ ; $I_C = 0$                                                    | –    | –    | 10   | mA            |
| $h_{FE}$                                                            | DC current gain                      | $V_{CE} = 5\text{ V}$ ; $I_C = 100\text{ mA}$ ;<br>see Fig.8                         | 6    | 13   | 30   |               |
| <b>Switching times in horizontal deflection circuit (see Fig.9)</b> |                                      |                                                                                      |      |      |      |               |
| $t_s$                                                               | storage time                         | $I_{CM} = 3\text{ A}$ ; $I_{B(end)} = 1\text{ A}$ ;<br>$L_B = 12\text{ }\mu\text{H}$ | –    | 6.5  | –    | $\mu\text{s}$ |
| $t_f$                                                               | fall time                            | $I_{CM} = 3\text{ A}$ ; $I_{B(end)} = 1\text{ A}$ ;<br>$L_B = 12\text{ }\mu\text{H}$ | –    | 0.7  | –    | $\mu\text{s}$ |

**Note**

1. Measured with a half-sinewave voltage (curve tracer).

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$T_{mb} = 25\text{ }^\circ\text{C}$ .

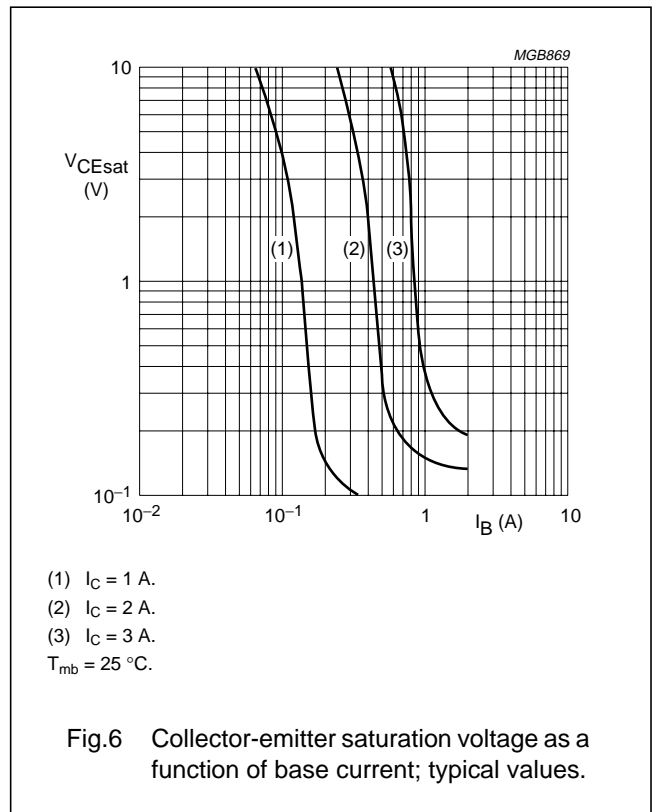
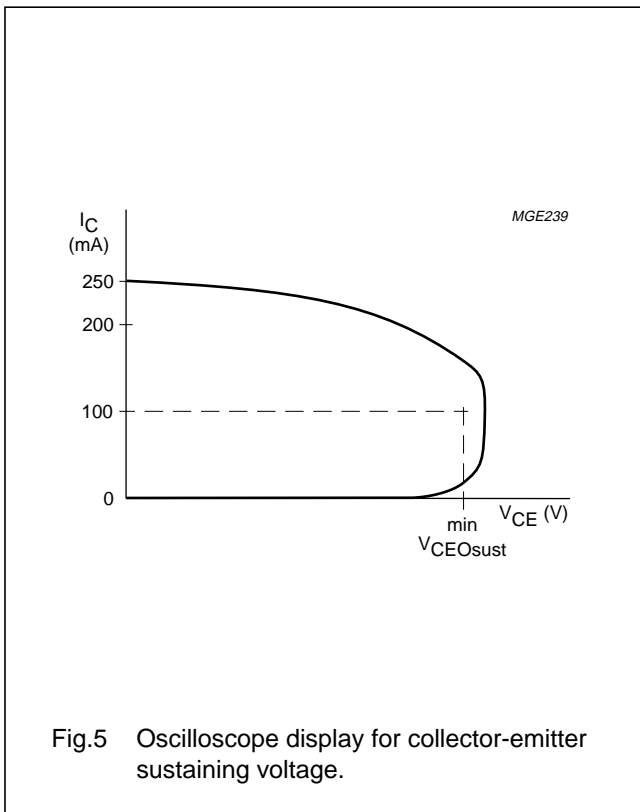
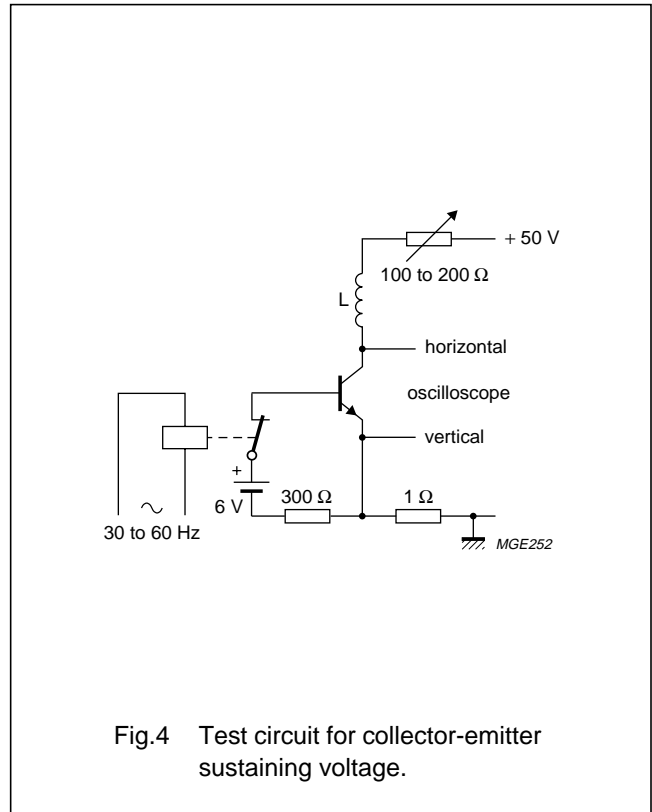
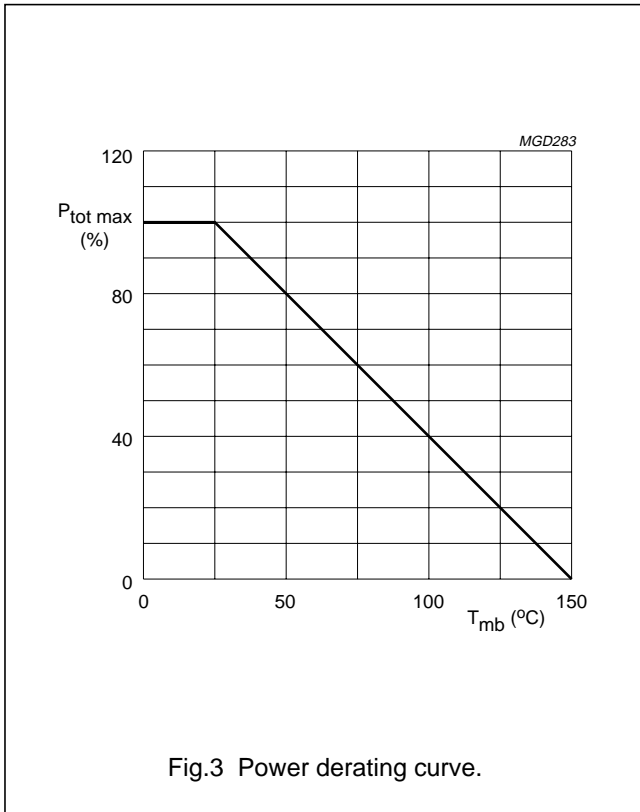
I - Region of permissible DC operation.

II - Permissible extension for repetitive pulse operation.

Fig.2 Forward bias SOAR.

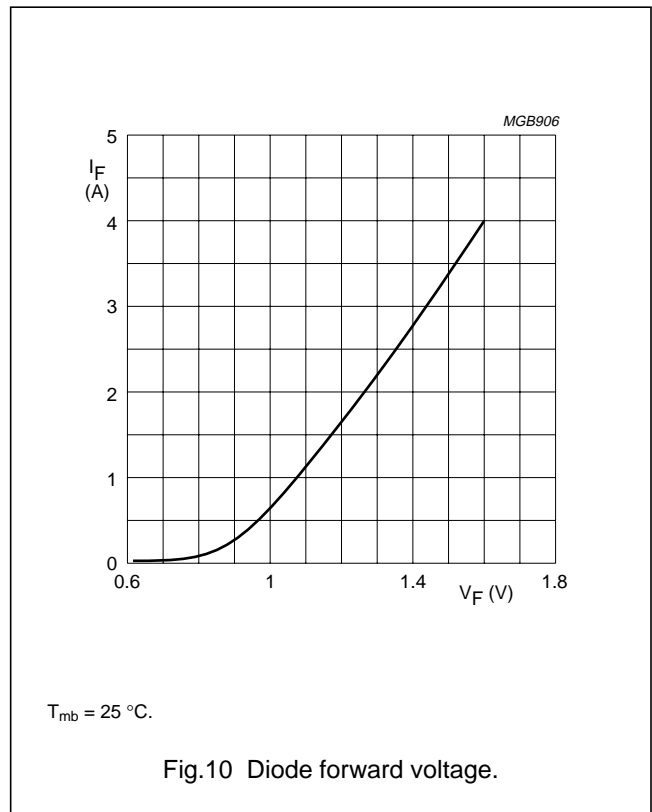
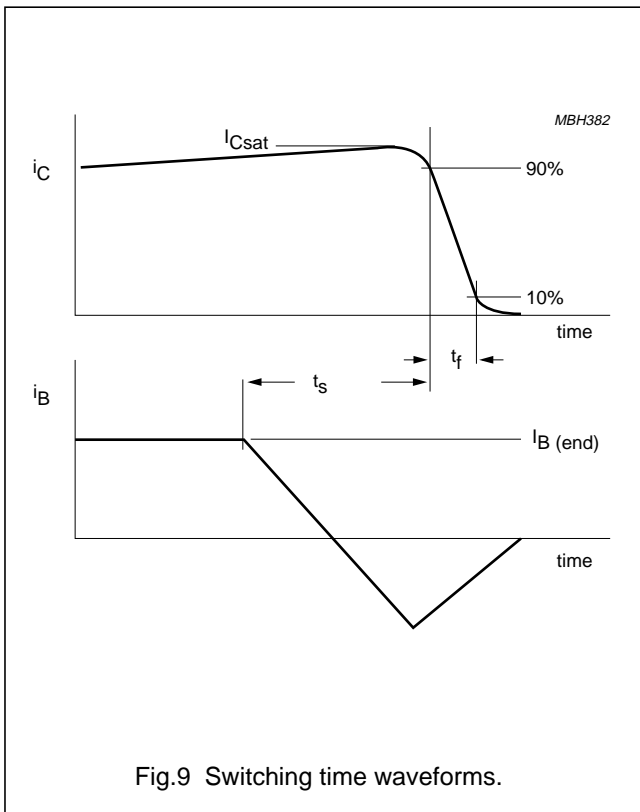
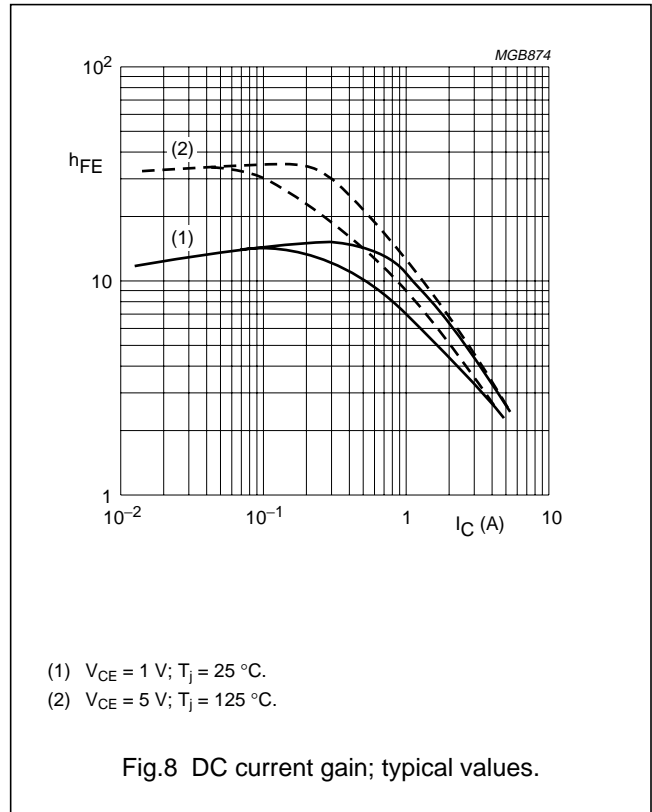
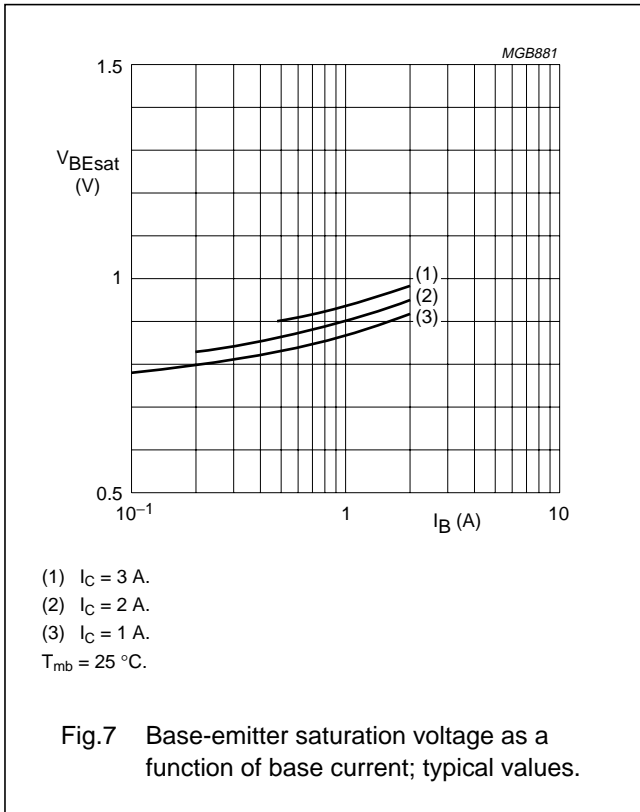
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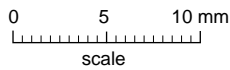
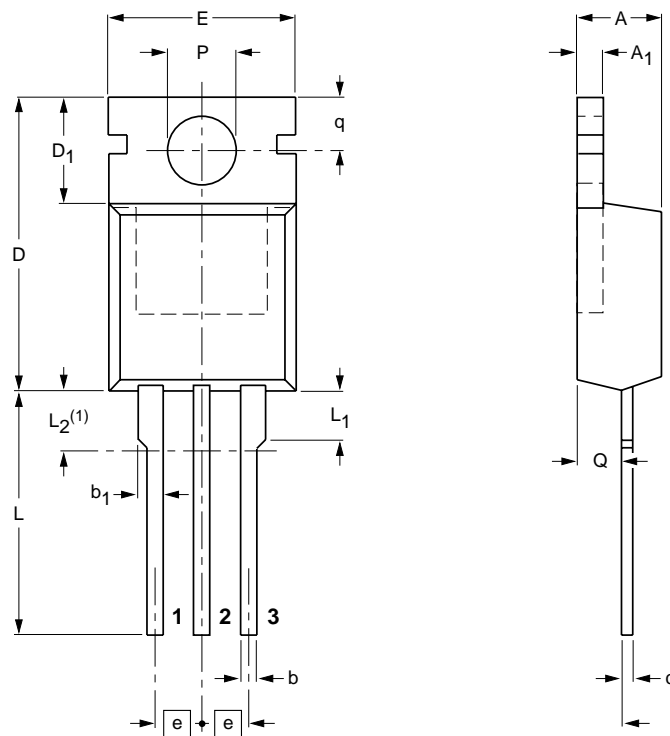
Silicon diffused power transistors

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PACKAGE OUTLINE

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220

SOT78



DIMENSIONS (mm are the original dimensions)

| UNIT | A          | A <sub>1</sub> | b          | b <sub>1</sub> | c          | D            | D <sub>1</sub> | E           | e    | L            | L <sub>1</sub> | L <sub>2</sub> <sup>(1)</sup><br>max. | P          | q          | Q          |
|------|------------|----------------|------------|----------------|------------|--------------|----------------|-------------|------|--------------|----------------|---------------------------------------|------------|------------|------------|
| mm   | 4.5<br>4.1 | 1.39<br>1.27   | 0.9<br>0.7 | 1.3<br>1.0     | 0.7<br>0.4 | 15.8<br>15.2 | 6.4<br>5.9     | 10.3<br>9.7 | 2.54 | 15.0<br>13.5 | 3.30<br>2.79   | 3.0                                   | 3.8<br>3.6 | 3.0<br>2.7 | 2.6<br>2.2 |

Note

1. Terminals in this zone are not tinned.

| OUTLINE<br>VERSION | REFERENCES |        |      |  | EUROPEAN<br>PROJECTION | ISSUE DATE |
|--------------------|------------|--------|------|--|------------------------|------------|
|                    | IEC        | JEDEC  | EIAJ |  |                        |            |
| SOT78              |            | TO-220 |      |  |                        | 97-06-11   |

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**DEFINITIONS**

| <b>Data sheet status</b>                                                                                                                                                                                                                                                                                                                                                                                                                                  |                                                                                       |
|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|---------------------------------------------------------------------------------------|
| Objective specification                                                                                                                                                                                                                                                                                                                                                                                                                                   | This data sheet contains target or goal specifications for product development.       |
| Preliminary specification                                                                                                                                                                                                                                                                                                                                                                                                                                 | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification                                                                                                                                                                                                                                                                                                                                                                                                                                     | This data sheet contains final product specifications.                                |
| <b>Limiting values</b>                                                                                                                                                                                                                                                                                                                                                                                                                                    |                                                                                       |
| Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability. |                                                                                       |
| <b>Application information</b>                                                                                                                                                                                                                                                                                                                                                                                                                            |                                                                                       |
| Where application information is given, it is advisory and does not form part of the specification.                                                                                                                                                                                                                                                                                                                                                       |                                                                                       |

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**NOTES**

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